#### TOSHIBA PHOTOCOUPLER GaAIAs IRED & PHOTO-TRIAC

# **TLP3064(S)**

# OFFICE MACHINE HOUSEHOLD USE EQUIPMENT TRIAC DRIVER **SOLID STATE RELAY**

The TOSHIBA TLP3064(S) consists of a zero voltage crossing turn-on photo-triac optically coupled to a GaAlAs infrared emitting diode in a six lead plastic DIP package.

Peak Off-State Voltage : 600V(Min) Trigger LED Current : 3mA(Max) On-State Current : 100mA(Max) • Isolation Voltage : 5000Vrms(Min)

: UL1577,File No.E67349 • UL Recognized

SEMKO Approved : SS EN60065

SS EN60950, File No.9841113

**BSI** Approved : BS EN60065, File No.8385

BS EN60950, File No.8386

Option (D4) type

VDE approved: DIN EN60747-5-2

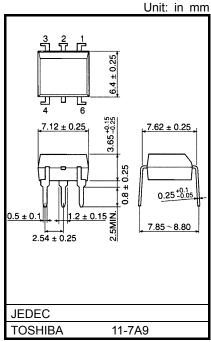
Approved No. 40009302

Maximum operating insulation voltage: 890VPK Highest permissible over voltage: 8000 Vpk

(Note): When a EN60747-5-2 approved type is needed, please designate the "Option (D4)"

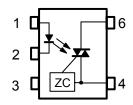
#### Construction Mechanical Rating

	7.62 mm pich Standard Type	10.16 mm pich TLPxxxxF Type
Creepage Distance	7.0 mm (Min)	8.0 mm (Min)
Clearance	7.0 mm (Min)	8.0 mm (Min)
Insulation Thickness	0.5 mm (Min)	0.5 mm (Min)



Weight: 0.39 g

### **Pin Configuration** (top view)



- 1: Anode
- 2: Cathode
- 3: N.C.
- 4:Terminal 1
- 6:Terminal 2

ZC:Zero-cross Circuit



## Absolute Maximum Ratings (Ta=25°C)

CHARACTERISTIC				RATING	UNIT	
	Forward Current	l <sub>F</sub>	30	mA		
Q	Forward Current Derating (Ta≥25°C)	ΔI <sub>F</sub> /°C	-0.3	mA /°C		
LED	Peak Forward Current (100µs pulse, 100pps)	IFP	1	Α		
	Reverse Voltage			5	V	
	Junction Temperature	Tj	125	°C		
	Off-State Output Terminal Voltage			600	V	
	On-State RMS Current	Ta=25°C	I <sub>T(RMS)</sub>	100	mA	
OR	On-State NWO Guirent	Ta=70°C	IT(RMS)	50		
DETECTOR	On-State Current Derating (Ta≥25°C)	ΔI <sub>T</sub> /°C	-1.1	mA /°C		
DE	Peak On-State Current (100µs pulse, 120pps)	I <sub>TP</sub>	2	Α		
	Peak Nonrepetitive Surge Current (Pw=10ms,DC=10	I <sub>TSM</sub>	1.2	Α		
	Junction Temperature	Tj	115	°C		
Stor	age Temperature Range	T <sub>stg</sub>	-55~150	°C		
Оре	rating Temperature Range	T <sub>opr</sub>	-40~100	°C		
Lea	d Soldering Temperature (10s)	T <sub>sol</sub>	260	°C		
Isola	ation Voltage (AC,1min. , R.H.≤60%)	BVS	5000	Vrms		

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

(Note 2) Device considered a two terminal device:Pins1, 2 and 3 shorted together and pin 4 and pin 6 shorted together.

## **Recommended Operating Conditions**

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	$V_{AC}$	_	_	240	$V_{\text{ac}}$
Forward Current	I <sub>F</sub>	4.5	6	7.5	mA
Peak On-State Current	I <sub>TP</sub>	_	_	1	Α
Operating Temperature	$T_{opr}$	-10	-	85	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.



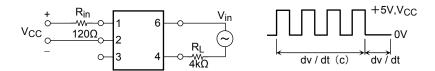
# Individual Electrical Characteristics (Ta=25°C)

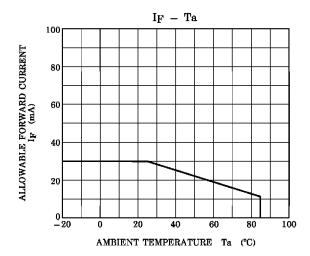
	CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
	Forward Voltage	V <sub>F</sub>	I <sub>F</sub> = 10 mA	1.2	1.4	1.7	V
LED	Reverse Current	I <sub>R</sub>	V <sub>R</sub> = 3 V	_	_	10	μA
	Capacitance	C <sub>T</sub>	V = 0, f=1MHz	_	30	_	pF
	Peak Off-State Current	I <sub>DRM</sub>	V <sub>DRM</sub> =600V	_	10	1000	nA
ᄶ	Peak On-State Voltage	$V_{TM}$	I <sub>TM</sub> =100mA	_	_	3.0	V
CTOR	Holding Current	I <sub>H</sub>	_	_	0.6	_	mA
DETE	Critical Rate of Rise of Off-State Voltage	dv/dt	Vin=240Vrms, Ta=85°C (Fig.1)	200	500	_	V/µs
	Critical Rate of Rise of Commutating Voltage	dv/dt(c)	Vin=60Vrms, IT=15mA (Fig.1)	_	0.2	_	V/µs

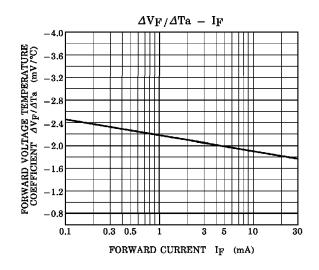
## **Coupled Electrical Characteristics (Ta=25°C)**

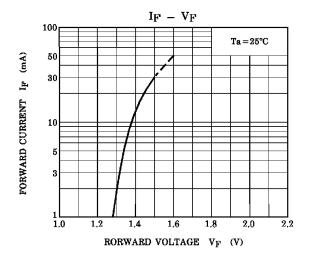
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Trigger LED Current	I <sub>FT</sub>	V <sub>T</sub> =6V ,Resistive Load	_	_	3	mA
Inhibit Voltage	V <sub>IH</sub>	IF=Rated I <sub>FT</sub>	_	_	50	V
Leakage in Inhibited State	I <sub>IH</sub>	IF=Rated I <sub>FT</sub> , V <sub>T</sub> =Rated V <sub>DRM</sub>	_	_	600	μΑ
Capacitance (Input to Output)	Cs	VS=0 , f=1MHz	_	0.8	_	pF
Isolation Resistance	Rs	VS=500V ,R.H.≤60%	1×10 <sup>12</sup>	10 <sup>14</sup>	_	Ω
	BVs	AC , 1minute	5000	_	_	Vrms
Isolation Voltage		AC , 1second,in oil	_	10000	_	
		DC , 1minute,in oil	_	10000	_	Vdc

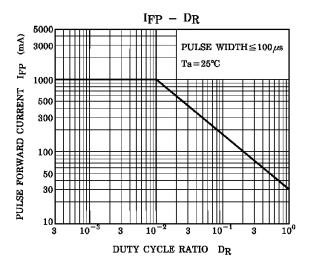
Fig. 1 dv / dt test circuit

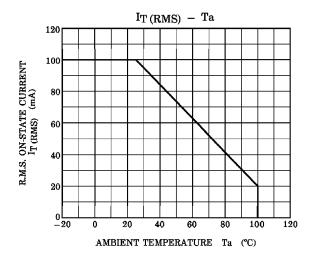


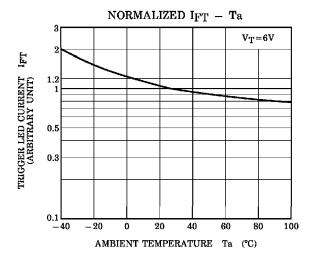


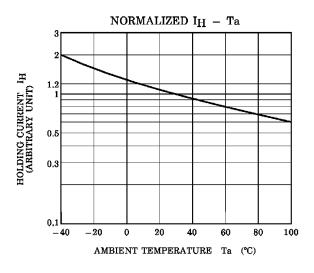


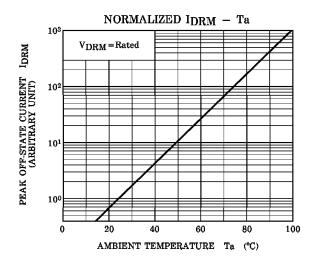


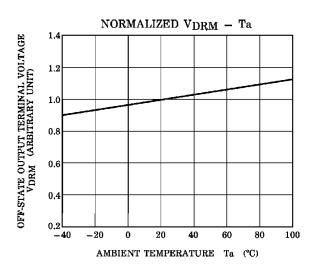


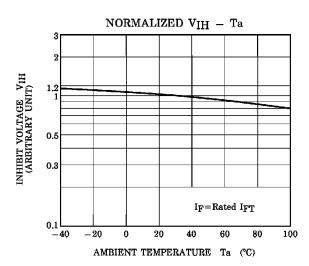


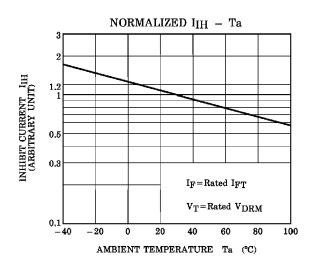












#### **RESTRICTIONS ON PRODUCT USE**

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